

DC to 5000 MHz, CASCADABLE SiGe HBT MMIC AMPLIFIER

RFMD SGA2463Z

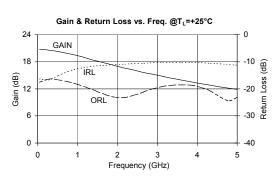
Package: SOT-363



Product Description

The SGA2463Z is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high F_T and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.





Features

- High Gain: 17.1dB at 1950MHz
- Cascadable 50Ω
- Operates from Single Supply
- Low Thermal Resistance Package

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Parameter	Specification			Unit	Condition		
Farameter	Min.	Тур.	Max.	UIIIL	Condition		
Small Signal Gain	18.0	20.0	22.0	dB	850MHz		
		17.1		dB	1950MHz		
Output Power at 1dB Compression		8.0		dBm	850MHz		
		7.2		dBm	1950MHz		
Output Third Intercept Point		20.1		dBm	850MHz		
		18.0		dBm	1950MHz		
Bandwidth Determined by Return Loss (>10dB)		5000		MHz			
Input Return Loss		11.1		dB	1950MHz		
Output Return Loss		23.1		dB	1950MHz		
Noise Figure		3.0		dB	1950MHz		
Device Operating Voltage	2.4	2.7	3.0	V			
Device Operating Current	17	20	23	mA			
Thermal Resistance (Junction - Lead)		255		°C/W			

 $Test\ Conditions:\ V_S=5\ V,\ I_D=20\ mA\ Typ.,\ OIP_3\ Tone\ Spacing=1\ MHz,\ P_{OUT}\ per\ tone=-5\ dBm,\ R_{BIAS}=120\ \Omega,\ T_L=25\ ^\circ C,\ Z_S=Z_L=50\ \Omega$

SGA2463Z



Absolute Maximum Ratings

Parameter	Rating	Unit
Max Device Current (I _D)	40	mA
Max Device Voltage (V _D)	5	V
Max RF Input Power	+18	dBm
Max Junction Temp (T _J)	+150	°C
Operating Temp Range (T _L)	-55 to +110	°C
Max Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

 $I_DV_D < (T_J - T_L) / R_{TH}$, j-l



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions of the device. tions is not implied.

The information in this publication is believed to be accurate and reliable. However, no

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65/EURFMD Green: RoHS compliant per EU Directive 2011/65/EU, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in

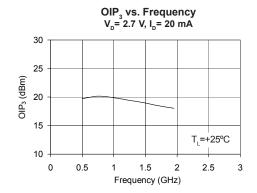
Typical Performance at Key Operating Frequencies

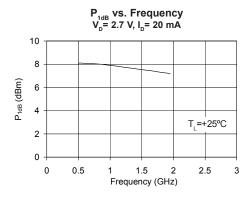
Parameter	Unit	100	500	850	1950	2400	3500
		MHz	MHz	MHz	MHz	MHz	MHz
Small Signal Gain	dB		20.3	20.0	17.1		
Output Third Order Intercept Point	dBm		19.7	20.1	18.0		
Output Power at 1dB Compression	dBm		8.1	8.0	7.2		
Input Return Loss	dB	16.7	15.3	13.2	11.1	10.8	10.3
Output Return Loss	dB	17.2	16.6	17.7	23.1	22.4	18.6
Reverse Isolation	dB	23.7	23.1	23.2	22.9	22.5	21.0
Noise Figure	dB		2.7	2.6	3.0		

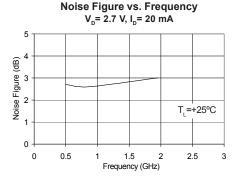
Test Conditions: $V_S = 5V$, $I_D = 20$ mA Typ., OIP $_3$ Tone Spacing = 1MHz, P_{OUT} per tone = -5dBm, $R_{BIAS} = 120\Omega$, $T_L = 25$ °C, $Z_S = Z_L = 50\Omega$

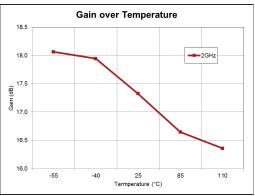








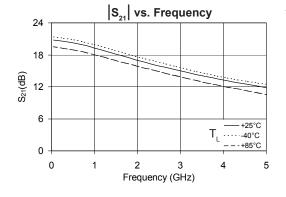


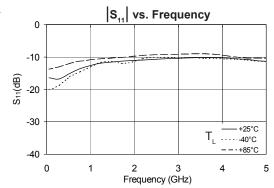


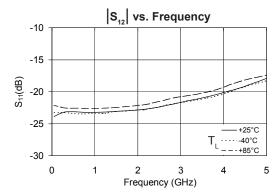
SGA2463Z

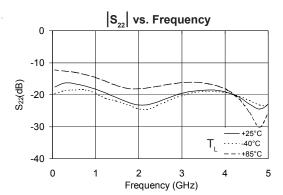


Typical RF Performance Over Temperature (Bias: $V_D=2.7V$, $I_D=20\,\text{mA}$ (Typ.))





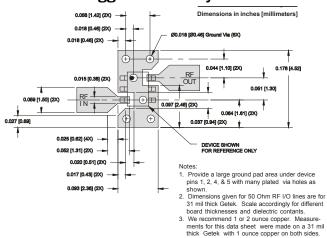






Pin	Function	Description
3	RF IN	RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation.
1, 2,	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.
4, 5		inductance.
6	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefor a DC-blocking capacitor is necessary for proper operation.

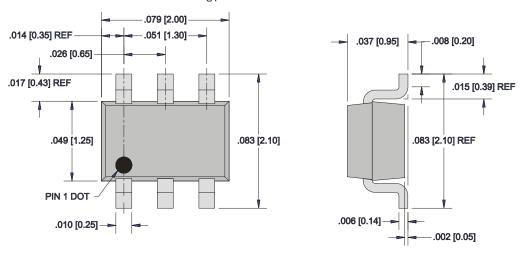
Suggested Pad Layout



Package Drawing

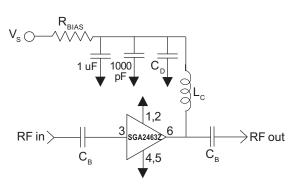
Dimensions in inches (millimeters)

Refer to drawing posted at www.rfmd.com for tolerances.





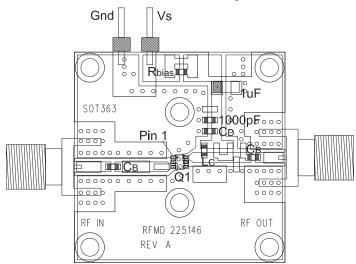
Application Schematic



Reference		Frequency (Mhz)					
Designator	500	850	1950				
C _B	220 pF	100 pF	68 pF				
C _D	100 pF	68 pF	22 pF				
L _c	68 nH	33 nH	22 nH				

Recommended Bias Resistor Values for I_D =20mA R_{BIAS} =(V_S - V_D) / I_D				
Supply Voltage(V _s)	5 V	6 V	8 V	10 V
R_{BIAS} 120Ω 160Ω 270Ω 360Ω				
Note: R _{BIAS} provides DC bias stability over temperature.				

Evaluation Board Layout

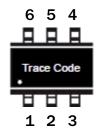


Mounting Instructions:

- 1. Use a large droung pad area near device pins 1, 2, 4, and 5 with plated through-holes as shown.
- 2. We recommend 1 or 2 ounces copper. Measurements for this data sheet were made on a 31mil thick FR-4 board with 1 ounce copper on both sides.



Part Identification Marking



Ordering Information

Ordering Code	Description
SGA2463Z	7" Reel with 3000 pieces
SGA2463ZSQ	Sample bag with 25 pieces
SGA2463ZSR	7" Reel with 100 pieces
SGA2463ZPCK1	850MHz, 5V Operation PCBA with 5-piece sample bag